

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

# 2SC1627

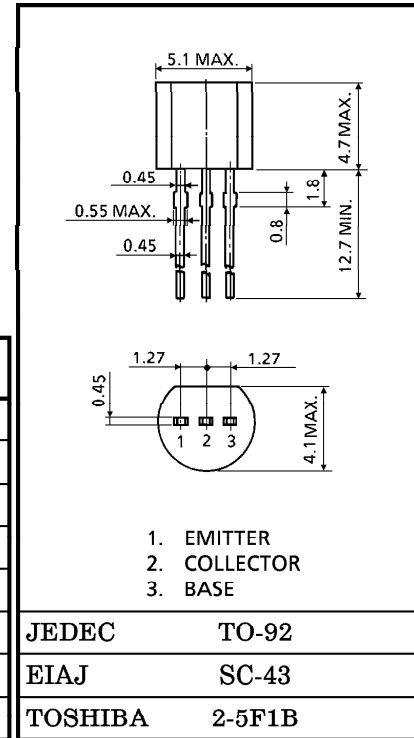
DRIVER STAGE AMPLIFIER APPLICATIONS  
VOLTAGE AMPLIFIER APPLICATIONS

Unit in mm

- Complementary to 2SA817
- Driver Stage Application of 20 to 25 Watts Amplifiers.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V <sub>CB0</sub>	80	V
Collector-Emitter Voltage	V <sub>CEO</sub>	80	V
Emitter-Base Voltage	V <sub>EBO</sub>	5	V
Collector Current	I <sub>C</sub>	300	mA
Base Current	I <sub>B</sub>	60	mA
Collector Power Dissipation	P <sub>C</sub>	600	mW
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	-55~125	°C



Weight : 0.21g

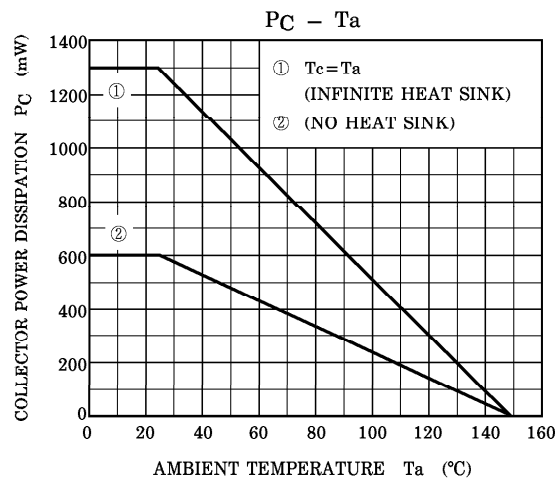
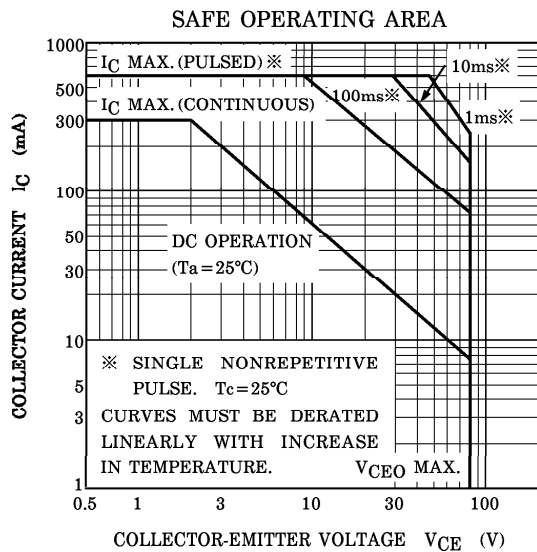
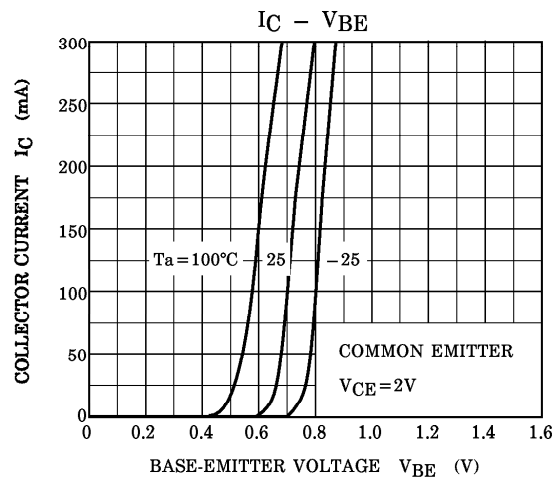
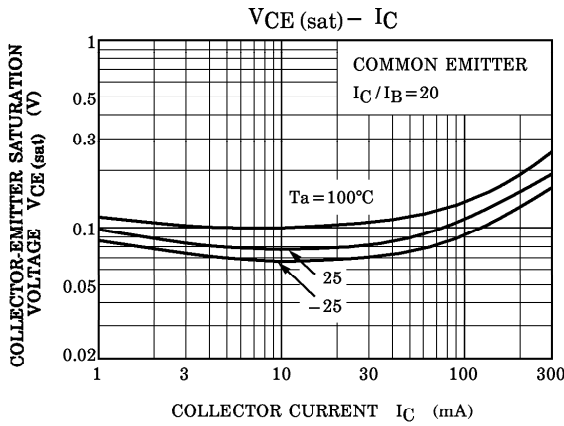
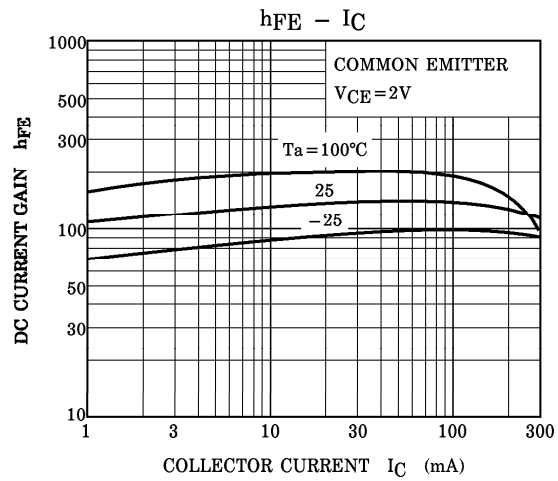
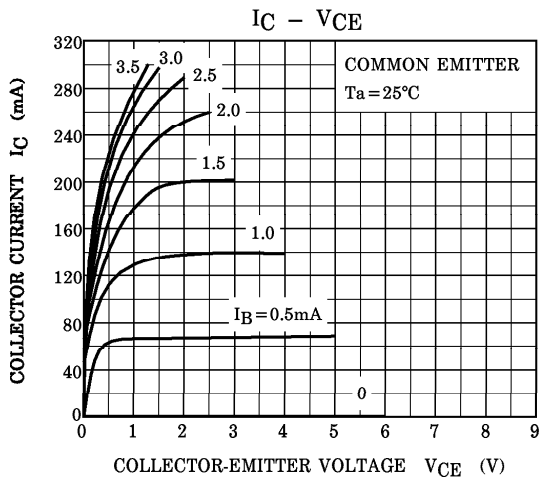
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I <sub>CBO</sub>	V <sub>CB</sub> = 50V, I <sub>E</sub> = 0	—	—	0.1	μA
Emitter Cut-off Current	I <sub>EBO</sub>	V <sub>EB</sub> = 5V, I <sub>C</sub> = 0	—	—	0.1	μA
Collector-Emitter Saturation Voltage	V (BR) CEO	I <sub>C</sub> = 5mA, I <sub>B</sub> = 0	80	—	—	V
DC Current Gain	h <sub>FE</sub> (1) (Note)	V <sub>CE</sub> = 2V, I <sub>C</sub> = 50mA	70	—	240	
	h <sub>FE</sub> (2)	V <sub>CE</sub> = 2V, I <sub>C</sub> = 200mA	40	—	—	
Collector-Emitter Saturation Voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> = 200mA, I <sub>B</sub> = 10mA	—	—	0.5	V
Base-Emitter Voltage	V <sub>BE</sub>	V <sub>CE</sub> = 2V, I <sub>C</sub> = 5mA	0.55	—	0.8	V
Transition Frequency	f <sub>T</sub>	V <sub>CE</sub> = 10V, I <sub>C</sub> = 10mA	—	100	—	MHz
Collector Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f = 1MHz	—	10	—	pF

Note : h<sub>FE</sub> (1) Classification    0 : 70~140,    Y : 120~240

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